

WHAT IS CLAIMED IS:

1. A method of designing a semiconductor device, said semiconductor device to be designed comprising:
 - 5 a semiconductor substrate;
 - an element isolation insulating film provided in a part of a main surface of said semiconductor substrate;
 - a gate structure provided on a part of said main surface of said semiconductor substrate, said gate structure being placed in an element forming region defined by said element isolation insulating film; and
 - 10 source/drain regions provided in said main surface of said semiconductor substrate in said element forming region, said source/drain regions forming a pair holding a channel forming region defined under said gate structure therebetween, wherein stress exerted on an area of said semiconductor substrate is controlled
 - 15 depending on a shape of said element forming region, said area of said semiconductor substrate holding said gate structure thereover.
2. The method according to claim 1, wherein
said element forming region includes in top view at least one projecting portion
20 provided along a perimeter of said element forming region.
3. The method according to claim 1, wherein
said element forming region includes in top view at least one recessed portion
provided along a perimeter of said element forming region.

4. The method according to claim 1, wherein

in top view, a corner of said element forming region is greater in curvature than
a corner of an element forming region defined by an element isolation insulating film
which is formed by a patterning process using a photomask having a rectangular opening

5 pattern.